

IN THE CLAIMS

Claim 1-12 (Canceled).

Claim 13 (Currently Amended): A liquid crystal display device, comprising:

a first transparent substrate;

a second transparent substrate facing the first transparent substrate;

a gate line arranged on the first transparent substrate along a first direction, the gate line includes a gate electrode extending from the gate line by a predetermined length along a second direction perpendicular to the first direction;

a data line arranged on the first transparent substrate along a second direction perpendicular to the first direction, the gate line and the data line perpendicularly crossing each other and defining a pixel region;

a thin film transistor arranged on the first transparent substrate and adjacent to the pixel region, the thin film transistor electrically connected to both the gate line and the data line;

a common line arranged on the first transparent substrate along the first direction parallel with and adjacent to the gate line, the common line having a protrusion extending toward the gate line along the second direction spaced apart from the gate line by a predetermined distance;

a first capacitor electrode overlapping a portion of the common line and the protrusion of the common line to form a first storage capacitor, the first capacitor electrode connected to the thin film transistor;

a pixel electrode formed within the pixel region, the pixel electrode contacting the first capacitor electrode;

a black matrix on the second transparent substrate, the black matrix covering the thin film transistor, the protrusion of the common line, and portions of the gate line and common line; and

a common electrode on the second transparent substrate to cover the black matrix,
wherein the predetermined length of the gate electrode is greater than the predetermined distance between the protrusion and the gate line.

Claim 14 (Original): The device according to claim 13, wherein the common line includes a same material as the gate line.

Claim 15 (Original): The device according to claim 14, wherein the common line and the gate line are simultaneously formed of an opaque metallic material.

Claim 16 (Original): The device according to claim 13, wherein the data line and the first capacitor electrode are simultaneously formed of a same material.

Claim 17 (Original): The device according to claim 13, further comprising a second capacitor electrode overlapping a portion of the gate line to form a second storage capacitor.

Claim 18 (Original): The device according to claim 17, wherein the first capacitor electrode and the second capacitor electrode are simultaneously formed of a same material.

Claim 19 (Original): The device according to claim 17, wherein the second capacitor electrode is electrically connected to the pixel electrode.

Claim 20 (Original): The device according to claim 13, wherein the protrusion extends from the common line toward the gate line along the second direction.

Claim 21 (Original): The device according to claim 20, wherein the protrusion is arranged between the gate line and the common line.

Claims 22-33 (Canceled).

Claim 34 (Currently Amended): A method for fabricating a liquid crystal display device, comprising the steps of:

forming a gate line on a first transparent substrate along a first direction, the gate line includes a gate electrode extending from the gate line by a predetermined length along a second direction perpendicular to the first direction;

forming a data line on the first transparent substrate along a second direction perpendicular to the first direction, the gate line and the data line perpendicularly crossing each other and defining a pixel region;

forming a thin film transistor on the first transparent substrate and adjacent to the pixel region, the thin film transistor is electrically connected to both the gate line and the data line;

forming a common line on the first transparent substrate along the first direction parallel with and adjacent to the gate line, the common line having a protrusion extending toward the gate line along the second direction spaced apart from the gate line by a predetermined distance;

forming a first capacitor electrode to overlap a portion of the common line and the protrusion of the common line to form a first storage capacitor, the first capacitor electrode connected to the thin film transistor;

forming a pixel electrode within the pixel region, the pixel electrode contacting the first capacitor electrode;

forming a black matrix on a second transparent substrate, the black matrix covering the thin film transistor, the protrusion of the common line, and portions of the gate line and common line;

forming a common electrode on the second transparent substrate to cover the black matrix; and

forming the first substrate to face the second substrate,

wherein the predetermined length of the gate electrode is greater than the predetermined distance between the protrusion and the gate line.

Claim 35 (Original): The method according to claim 34, wherein the common line includes a same material as the gate line.

Claim 36 (Original): The method according to claim 35, wherein the common line and the gate line are simultaneously formed of an opaque metallic material.

Claim 37 (Original): The method according to claim 34, wherein the steps of forming the data line and the first capacitor electrode are simultaneously formed of a same material.

Claim 38 (Original): The method according to claim 34, further comprising a step of forming a second capacitor electrode to overlap a portion of the gate line to form a second storage capacitor.

Claim 39 (Original): The method according to claim 38, wherein the step of forming a first capacitor electrode and the step of forming a second capacitor electrode are simultaneously performed using a same material.

Claim 40 (Original): The method according to claim 38, wherein the second capacitor electrode is electrically connected to the pixel electrode.

Claim 41 (Original): The method according to claim 34, wherein the protrusion extends from the common line toward the gate line along the second direction.

Claim 42 (Original): The method according to claim 41, wherein the protrusion is arranged between the gate line and the common line.

Claim 43 (New): A liquid crystal display device, comprising:

- a first transparent substrate;

- a second transparent substrate facing the first transparent substrate;

- a gate line arranged on the first transparent substrate along a first direction;

- a data line arranged on the first transparent substrate along a second direction perpendicular to the first direction, the gate line and the data line perpendicularly crossing each other and defining a pixel region;

- a thin film transistor arranged on the first transparent substrate and adjacent to the pixel region, the thin film transistor electrically connected to both the gate line and the data line;

a common line arranged on the first transparent substrate along the first direction parallel with and adjacent to the gate line;

a protrusion extending from the common line toward the gate line along the second direction;

a pixel electrode formed within the pixel region;

a black matrix on the second transparent substrate, the black matrix covering the thin film transistor and portions of the gate line and common line; and

a common electrode on the second transparent substrate to cover the black matrix, wherein the black matrix covers an area between the gate line and the protrusion.

Claim 44 (New): The device according to claim 43, further comprising a first capacitor electrode overlapping a portion of the common line to form a first storage capacitor, wherein the first capacitor electrode is connected to the thin film transistor.

Claim 45 (New): The device according to claim 44, further comprising a second capacitor electrode overlapping a portion of the gate line to form a second storage capacitor.

Claim 46 (New): The device according to claim 45, wherein the first capacitor electrode and the second capacitor electrode are simultaneously formed of a same material.

Claim 47 (New): The device according to claim 45, wherein the second capacitor electrode is electrically connected to the pixel electrode at a first region.

Claim 48 (New): The device according to claim 47, wherein the black matrix overlaps the first region.

Claim 49 (New): The device according to claim 43, wherein the common line and the adjacent gate line are separated by a gap and the black matrix overlaps the gap.

Claim 50 (New): The device according to claim 43, wherein the protrusion is arranged between the gate line and the common line.

Claim 51 (New): A method of fabricating a liquid crystal display device, comprising:

- a first transparent substrate;
- a second transparent substrate facing the first transparent substrate;
- forming a gate line arranged on a first transparent substrate along a first direction;
- forming a data line arranged on the first transparent substrate along a second direction perpendicular to the first direction, the gate line and the data line perpendicularly crossing each other and defining a pixel region;
- forming a thin film transistor on the first transparent substrate and adjacent to the pixel region, the thin film transistor electrically connected to both the gate line and the data line;

forming a common line on the first transparent substrate along the first direction parallel with and adjacent to the gate line, the common line includes a protrusion extending from the common line toward the gate line along the second direction;

forming a pixel electrode formed within the pixel region;

forming a black matrix on a second transparent substrate, the black matrix covering the thin film transistor and portions of the gate line and common line; and

forming a common electrode on the second transparent substrate to cover the black matrix,

wherein the black matrix covers an area between the gate line and the protrusion.

Claim 52 (New): The method according to claim 51, further comprising forming a first capacitor electrode overlapping a portion of the common line to form a first storage capacitor, wherein the first capacitor electrode is connected to the thin film transistor.

Claim 53 (New): The method according to claim 52, further comprising forming a second capacitor electrode overlapping a portion of the gate line to form a second storage capacitor.

Claim 54 (New): The method according to claim 53, wherein the first capacitor electrode and the second capacitor electrode are simultaneously formed of a same material.

Claim 55 (New): The method according to claim 53, wherein the second capacitor electrode is electrically connected to the pixel electrode at a first region.

Claim 56 (New): The method according to claim 55, wherein the black matrix overlaps the first region.

Claim 57 (New): The method according to claim 51, wherein the common line and the adjacent gate line are separated by a gap and the black matrix overlaps the gap.

Claim 58 (New): The method according to claim 51, wherein the protrusion is arranged between the gate line and the common line.